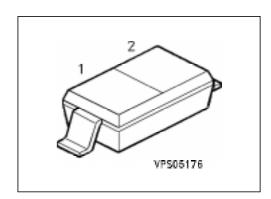
SIEMENS

Silicon Variable Capacitance Diode

BB 640

• For Hyperband TV/VTR tuners, Bd I



Туре	Ordering Code	Pin Configuration		Marking	Package
	(tape and reel)	1	2		
BB 640	Q62702-B589	С	A	red S	SOD-323

Maximum Ratings

Parameter	Symbol	Values	Unit
Reverse voltage	V_{R}	30	V
Reverse voltage ($R \ge 5 \text{ k}\Omega$)	V_{RM}	35	
Forward current	<i>I</i> F	20	mA
Operating temperature range	Top	- 55 + 150	°C
Storage temperature range	Tstg	- 55 + 150	

Thermal Resistance

Junction - ambient	$oldsymbol{R}$ th JA	≤ 450	K/W

Electrical Characteristics

at $T_A = 25$ °C, unless otherwise specified.

Parameter	Symbol		Values		
		min.	typ.	max.	
Reverse current $V_R = 30 \text{ V}$ $V_R = 30 \text{ V}$, $T_A = 85 \text{ °C}$	<i>I</i> R	 - -	_ _	10 200	nA
Diode capacitance, f = 1 MHz $V_R = 1 \text{ V}$ $V_R = 28 \text{ V}$	Ст	62 2.9		76 3.4	pF
Capacitance ratio $V_R = 1 \text{ V}, 28 \text{ V}, f = 1 \text{ MHz}$	<u>С</u> т1 <u>С</u> т28	19.5	_	25	-
Capacitance matching $V_R = 1 \text{ V} \dots 28 \text{ V}, f = 1 \text{ MHz}$	$\frac{\Delta C_{T}}{C_{T}}$	_	_	2.5	%
Series resistance $C_T = 30 \text{ pF}, f = 100 \text{ MHz}$	r _s	_	1.15	_	Ω
Series inductance	Ls	_	2	_	nH

Diode capacitance $C_T = f(V_R)$

f = 1 MHz

